

# PMEG3002TV

# $0.2~\mathrm{A}~\mathrm{very}~\mathrm{low}~\mathrm{V_F}~\mathrm{MEGA}~\mathrm{Schottky}~\mathrm{barrier}~\mathrm{dual}~\mathrm{rectifier}~\mathrm{in}~\mathrm{SOT}666~\mathrm{package}$

Rev. 02 — 15 January 2010

**Product data sheet** 

# 1. Product profile

### 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier dual rectifier with an integrated guard ring for stress protection, encapsulated in a SOT666 ultra small and flat lead Surface Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package		Configuration
	NXP	JEITA	
PMEG3002TV	SOT666	-	dual isolated

#### 1.2 Features

Forward current: ≤ 0.2 A

■ Reverse voltage: ≤ 30 V

Very low forward voltage

Ultra small and flat lead SMD plastic package

### 1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Inverse polarity protection
- Low power consumption applications

### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
I <sub>F</sub>	forward current	$T_{amb} \leq 25 ^{\circ}C$	<u>[1]</u> -	-	0.2	Α
$V_R$	reverse voltage		-	-	30	V
V <sub>F</sub>	forward voltage	$I_F = 200 \text{ mA}$	[2] _	420	480	mV

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 





# 2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Symbol
1	anode (diode 1)		
2	not connected	6 5 4	6 5 4
3	cathode (diode 2)		\frac{1}{2} \qquad \frac{1}{2} \qquad
4	anode (diode 2)		
5	not connected	1 2 3	1 2 3 <i>006aaa440</i>
6	cathode (diode 1)	1 2 3	

# 3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PMEG3002TV	-	plastic surface mounted package; 6 leads	SOT666

# 4. Marking

Table 5. Marking codes

Type number	Marking code
PMEG3002TV	2M



# 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diod	е				
V <sub>R</sub>	reverse voltage		-	30	V
l <sub>F</sub>	forward current	$T_{amb} \le 25  ^{\circ}C$	[1] -	0.2	Α
I <sub>FRM</sub>	repetitive peak forward current	$t_p \leq \text{1 ms; } \delta \leq 0.25$	-	1	Α
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; t <sub>p</sub> = 8 ms	[1] -	2.5	Α
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u> _	200	mW
			[2] _	300	mW
Per devi	ce				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u> _	300	mW
			[2] _	400	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		<del>-</del> 65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

### 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device	e						
$R_{th(j\text{-}a)} \qquad \text{thermal resistance from } \\ \text{junction to ambient}$			[1][2]	-	-	416	K/W
	junction to ambient		[1][3]	-	-	318	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		<u>[4]</u>	-	-	195	K/W

<sup>[1]</sup> For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses. Nomograms for determining the reverse power losses P<sub>R</sub> and I<sub>F(AV)</sub> rating are available on request.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

<sup>[4]</sup> Soldering point of cathode tab.



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#### **Characteristics 7**.

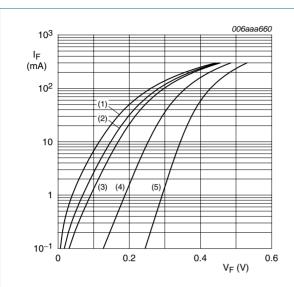
**Product data sheet** 

Table 8. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

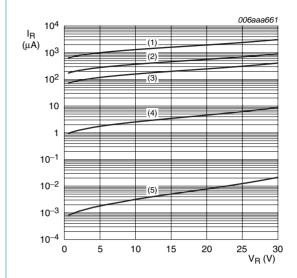
Parameter	Conditions	Min	Tvp	Max	Unit
)			- 7 P		
forward voltage		[1]			
	$I_F = 0.1 \text{ mA}$	-	130	190	mV
	I <sub>F</sub> = 1 mA	-	190	250	mV
	I <sub>F</sub> = 10 mA	-	255	300	mV
	I <sub>F</sub> = 100 mA	-	355	400	mV
	I <sub>F</sub> = 200 mA	-	420	480	mV
reverse current	V <sub>R</sub> = 10 V	-	3	10	μΑ
	V <sub>R</sub> = 30 V	-	10	30	μΑ
	V <sub>R</sub> = 10 V; T <sub>amb</sub> = 100 °C	-	400	-	μΑ
diode capacitance	$V_R = 1 V; f = 1 MHz$	-	20	25	pF
	forward voltage	forward voltage $I_F = 0.1 \text{ mA}$ $I_F = 1 \text{ mA}$ $I_F = 10 \text{ mA}$ $I_F = 100 \text{ mA}$ $I_F = 200 \text{ mA}$ reverse current $V_R = 10 \text{ V}$ $V_R = 30 \text{ V}$ $V_R = 10 \text{ V}; T_{amb} = 100 \text{ °C}$			

<sup>[1]</sup> Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 



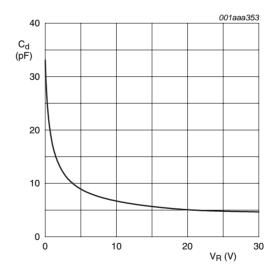
- (1)  $T_{amb} = 125 \, ^{\circ}C$
- (2) T<sub>amb</sub> = 100 °C
- (3)  $T_{amb} = 85 \, ^{\circ}C$
- (4)  $T_{amb} = 25 \, ^{\circ}C$
- (5)  $T_{amb} = -40 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1)  $T_{amb} = 125 \, ^{\circ}C$
- (2)  $T_{amb} = 100 \, ^{\circ}C$
- (3)  $T_{amb} = 85 \, ^{\circ}C$
- (4)  $T_{amb} = 25 \, ^{\circ}C$
- (5)  $T_{amb} = -40 \, ^{\circ}C$

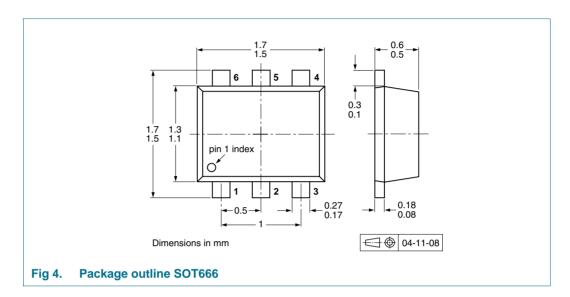
Fig 2. Reverse current as a function of reverse voltage; typical values



 $T_{amb} = 25 \, ^{\circ}C; f = 1 \, MHz$ 

Fig 3. Diode capacitance as a function of reverse voltage; typical values

# 8. Package outline



# 9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

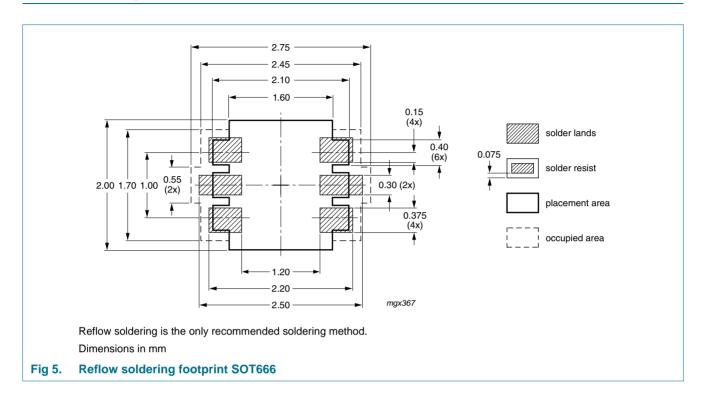
Type number	Package	Description Packing quantity		ntity
			4000	8000
PMEG3002TV	SOT666	2 mm pitch, 8 mm tape and reel	-	-315
		4 mm pitch, 8 mm tape and reel	-115	-

[1] For further information and the availability of packing methods, see Section 13.

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# 10. Soldering





# 11. Revision history

### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG3002TV_2	20100115	Product data sheet	-	PMEG3002TV_1
Modifications:		eet was changed to reflect w legal definitions and disc		
PMEG3002TV_1	20051021	Product data sheet	-	-

# 12. Legal information

### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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